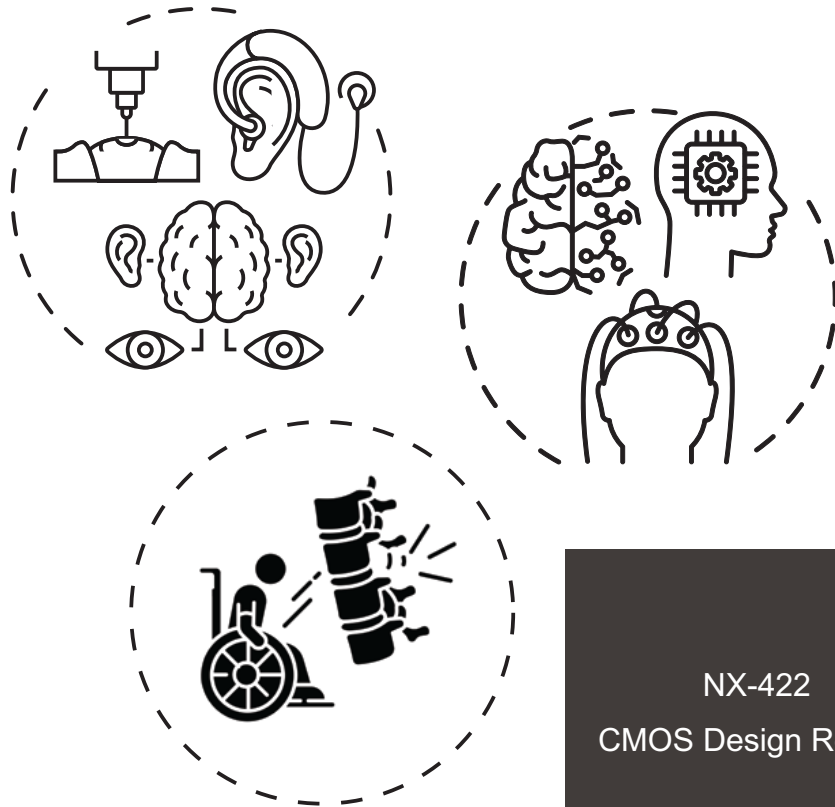
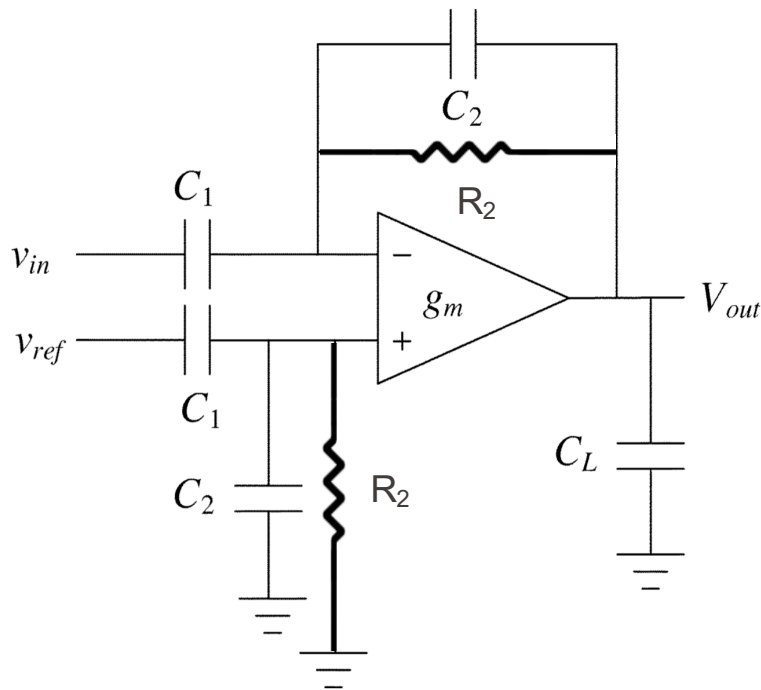




Neural Interfaces

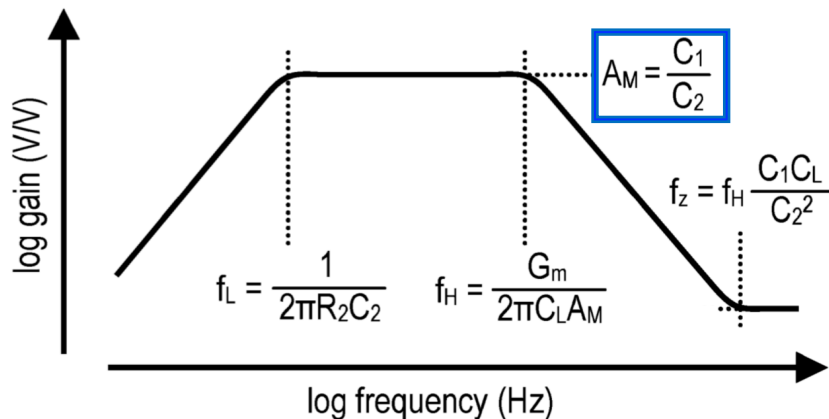
NX-422
CMOS Design Review

Mahsa Shoaran
IEM and Neuro-X Institutes

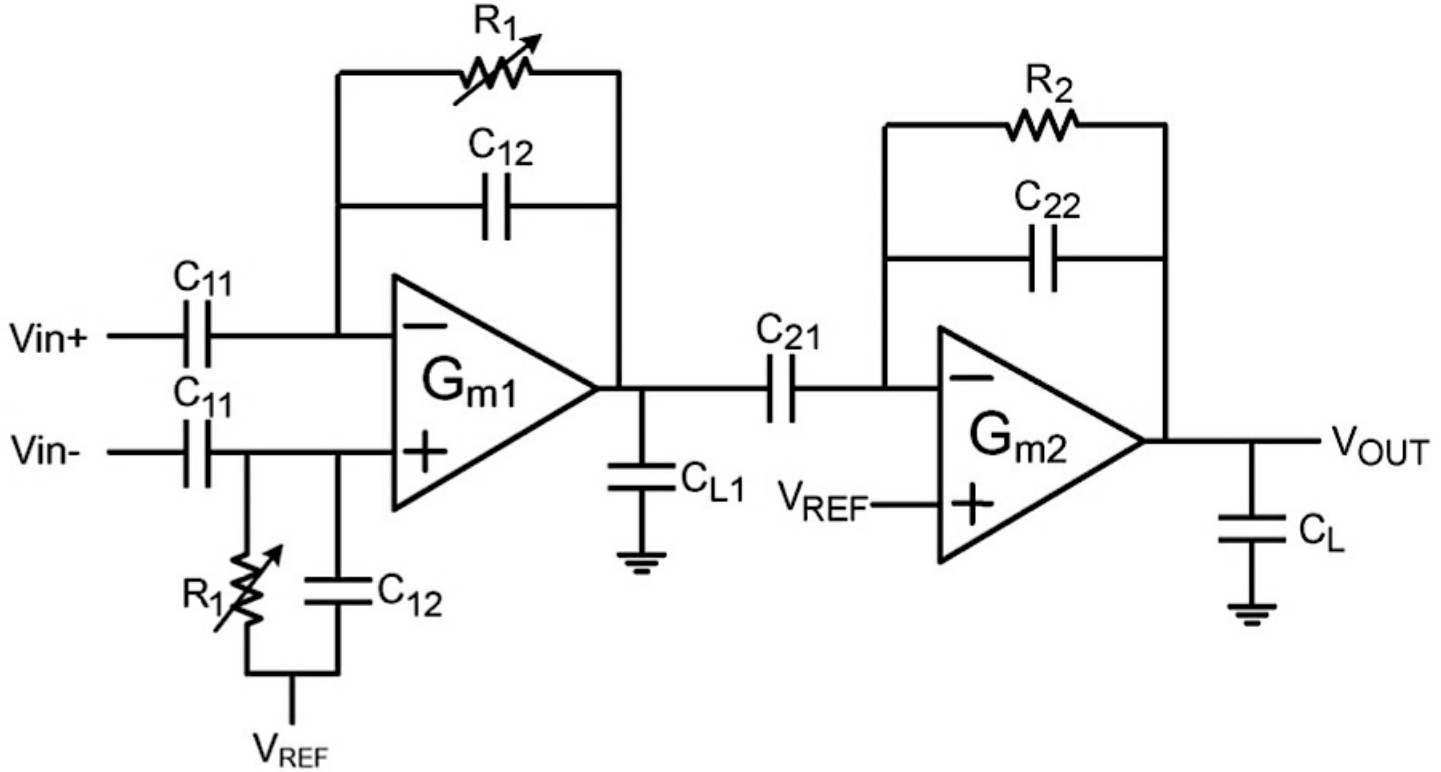


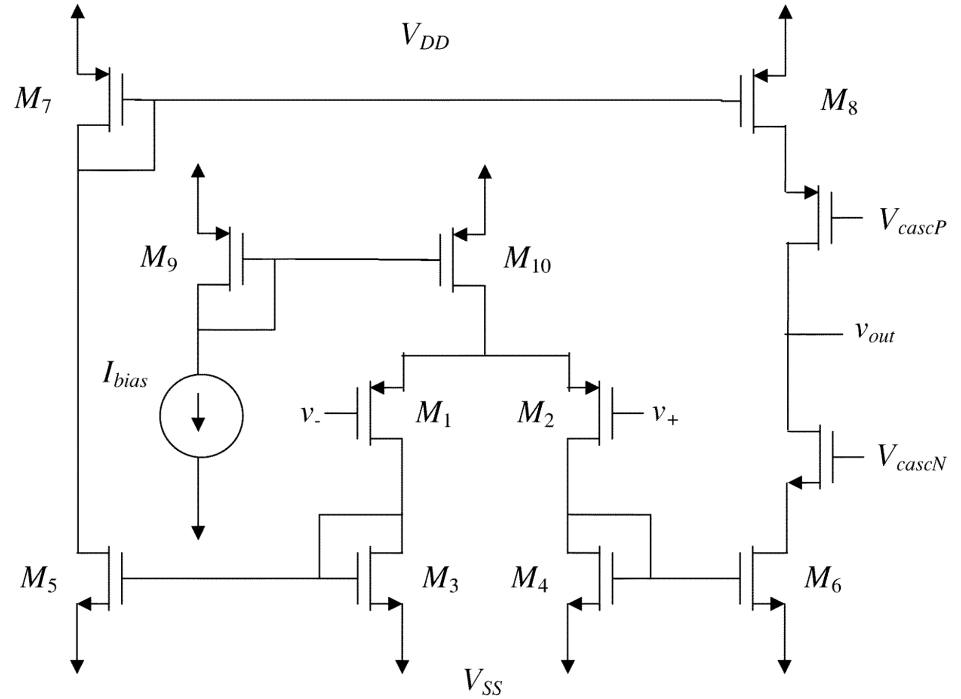
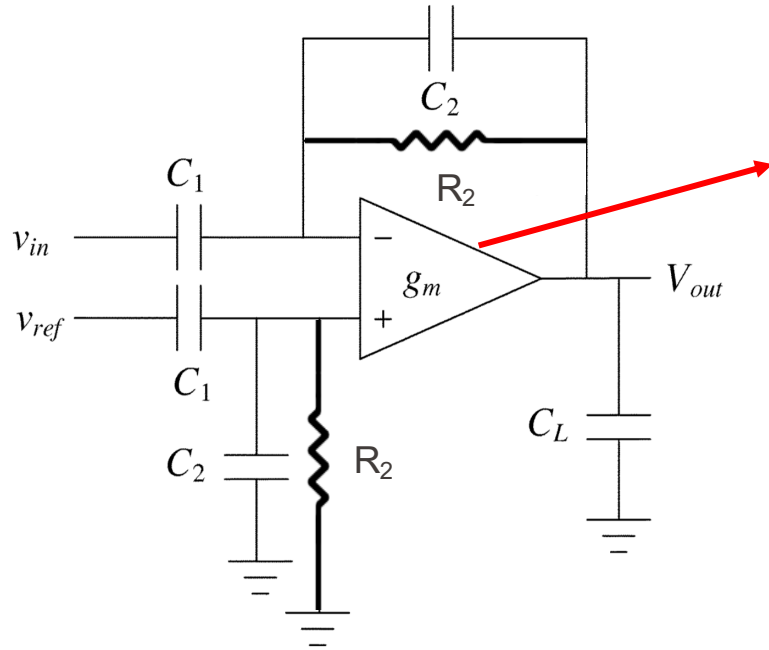
$$\frac{v_{out}}{v_{in+} - v_{in-}} = \frac{C_1}{C_2} \cdot \frac{1 - sC_2/G_m}{\left(\frac{1}{sR_2C_2} + 1\right) \left(s\frac{C_L C_1}{G_m C_2} + 1\right)}$$

$$= A_M \frac{1 - s/(2\pi f_z)}{\left(\frac{2\pi f_L}{s} + 1\right) \left(\frac{s}{2\pi f_H} + 1\right)}$$

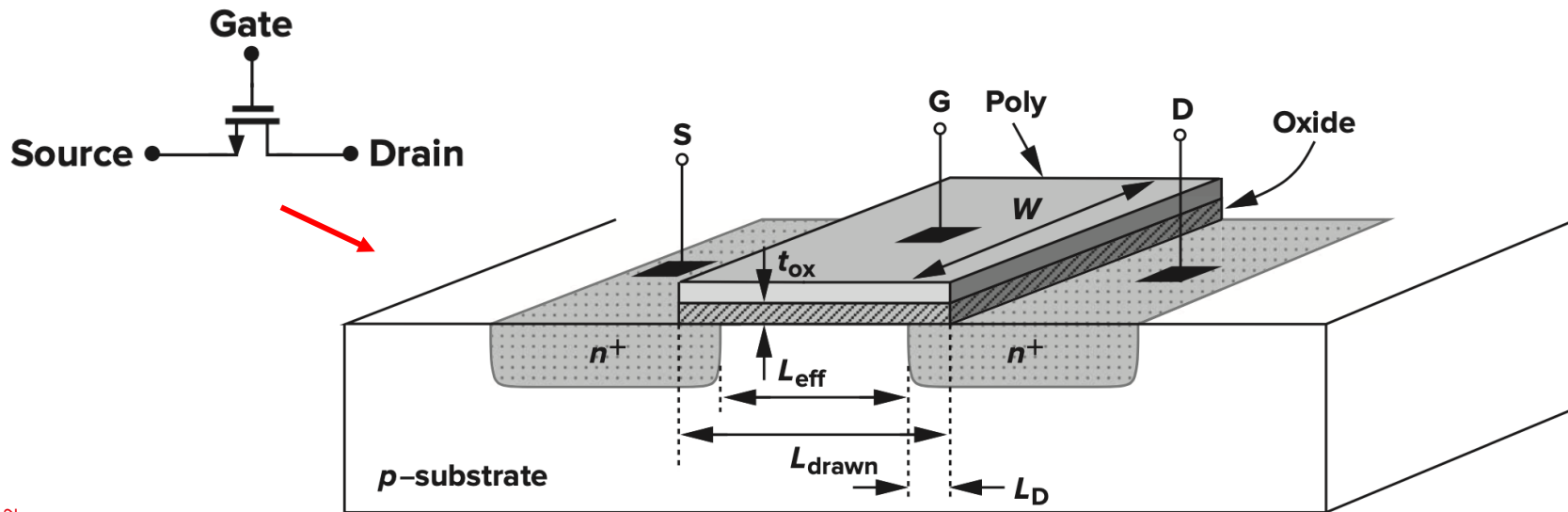


Recap: Neural Amplifier: Multi-Stage, Higher Gain

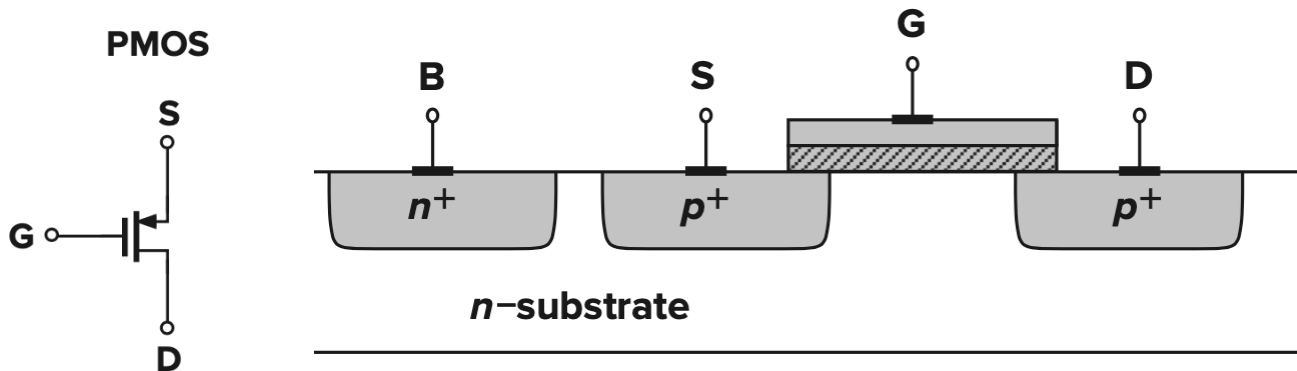




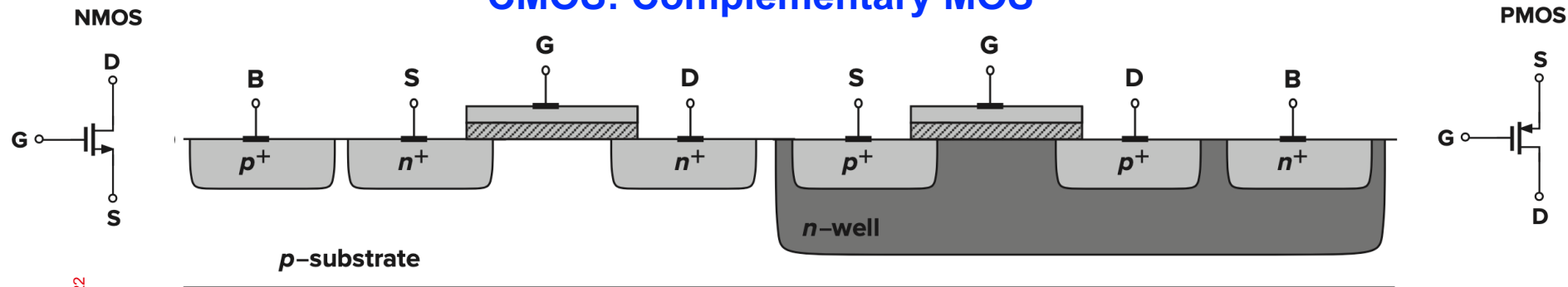
- **MOS: Metal-Oxide-Semiconductor** field-effect transistor (also called MOSFET)
- An n-type MOS (**NMOS**) device on a **p-type substrate**
 - a heavily-doped polysilicon (**conductor**) operating as the **gate**
 - a thin layer of silicon dioxide (SiO_2) **insulating** the gate from the substrate
 - two heavily-doped **n regions**: **source** and **drain** terminals



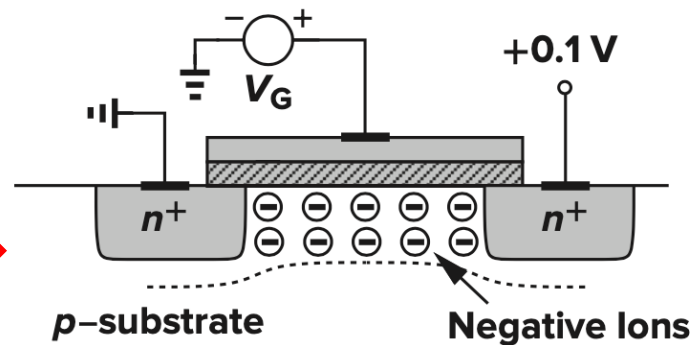
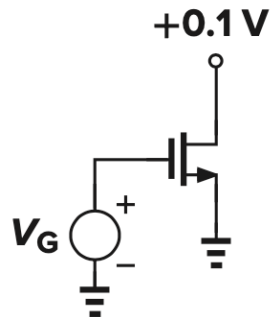
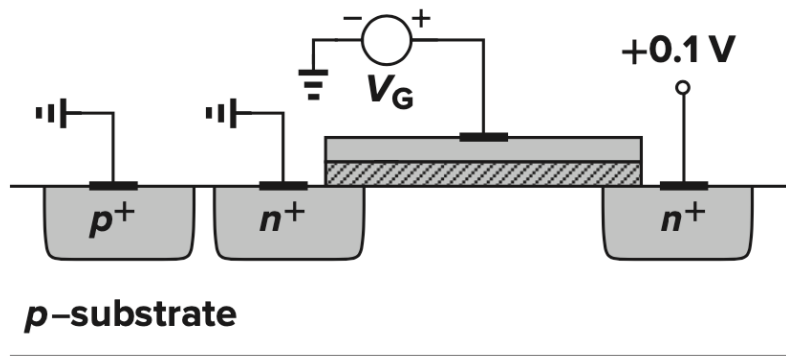
Recap: CMOS: NMOS + PMOS



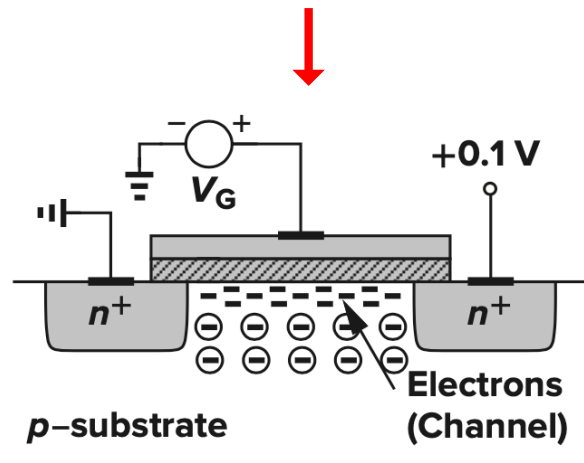
CMOS: Complementary MOS



Recap: MOS threshold voltage

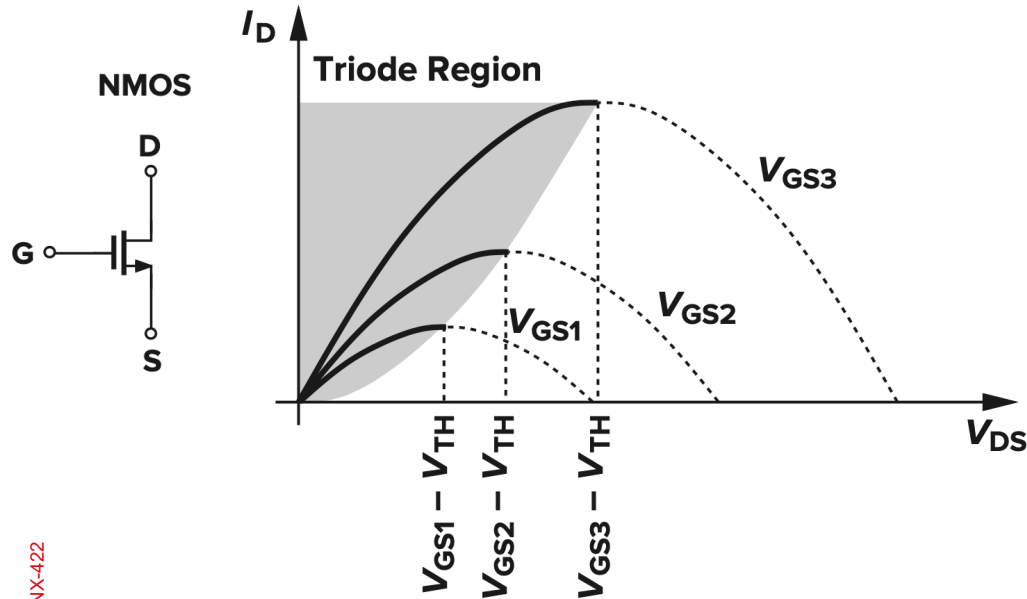


$$V_{TH} = \Phi_{MS} + 2\Phi_F + \frac{Q_{dep}}{C_{ox}}$$

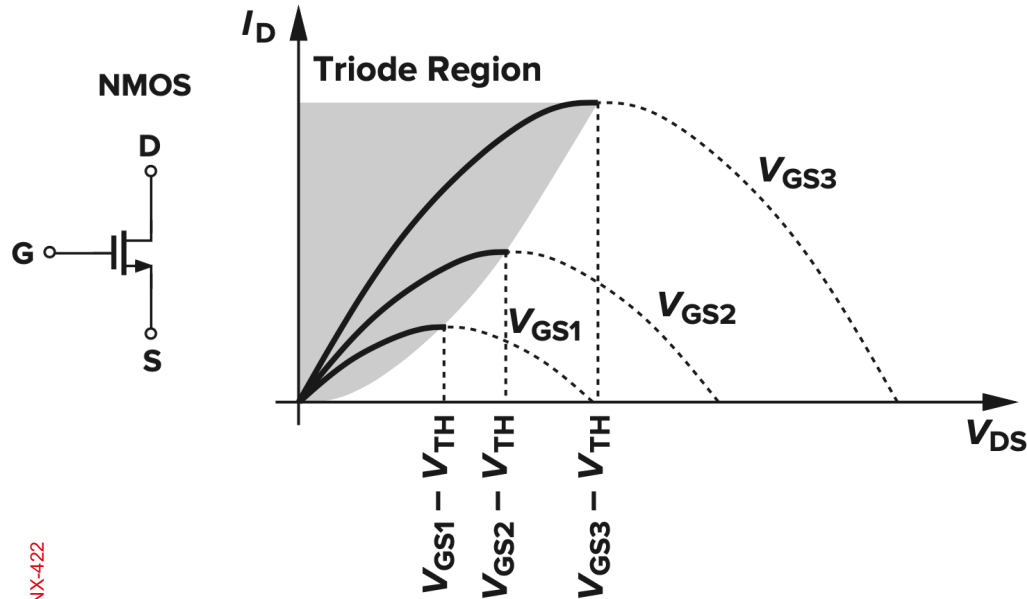


$$V_{DS} \leq V_{GS} - V_{TH}$$

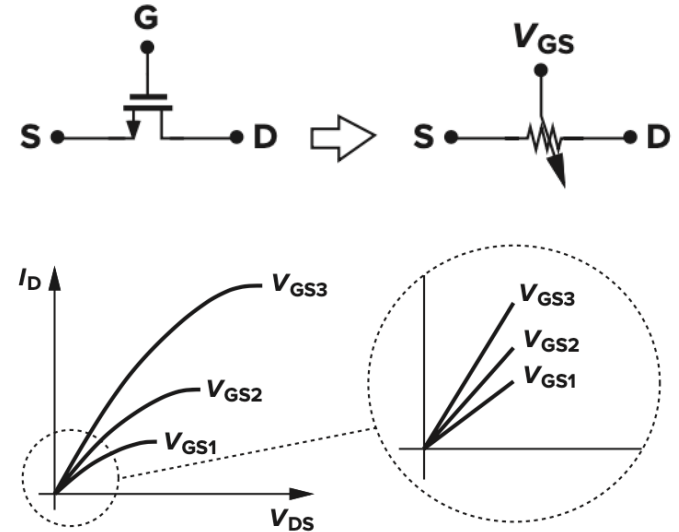
$$I_D = \mu_n C_{ox} \frac{W}{L} \left[(V_{GS} - V_{TH}) V_{DS} - \frac{1}{2} V_{DS}^2 \right]$$



$$V_{DS} \leq V_{GS} - V_{TH}$$

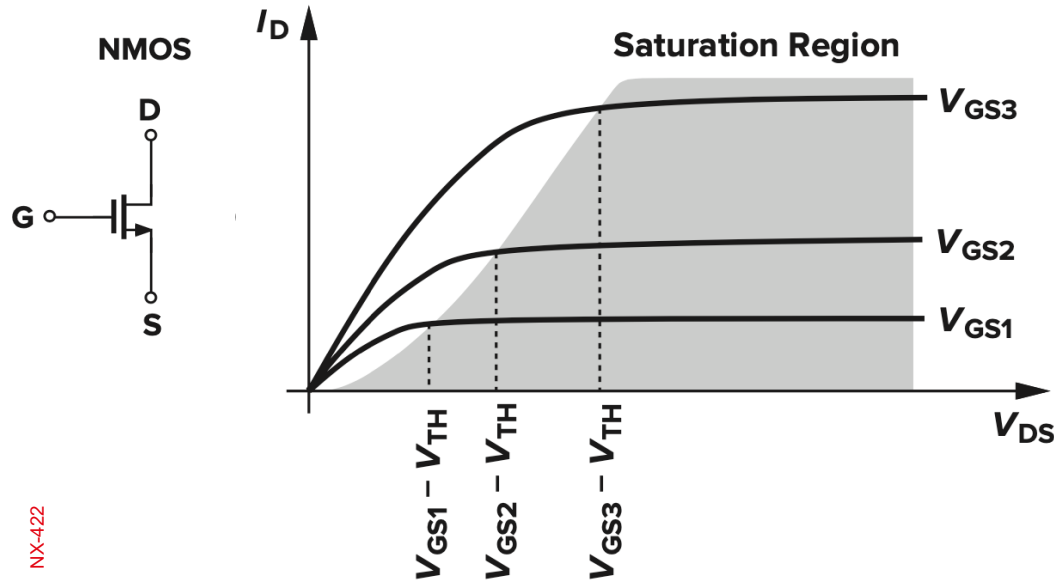


$$R_{on} = \frac{1}{\mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})}$$

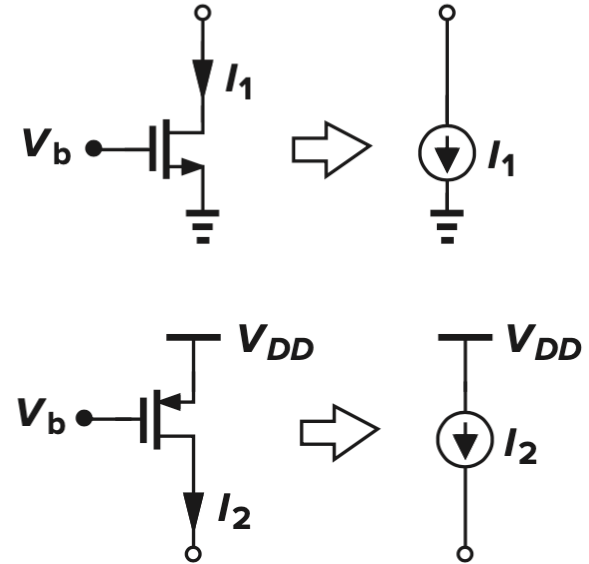
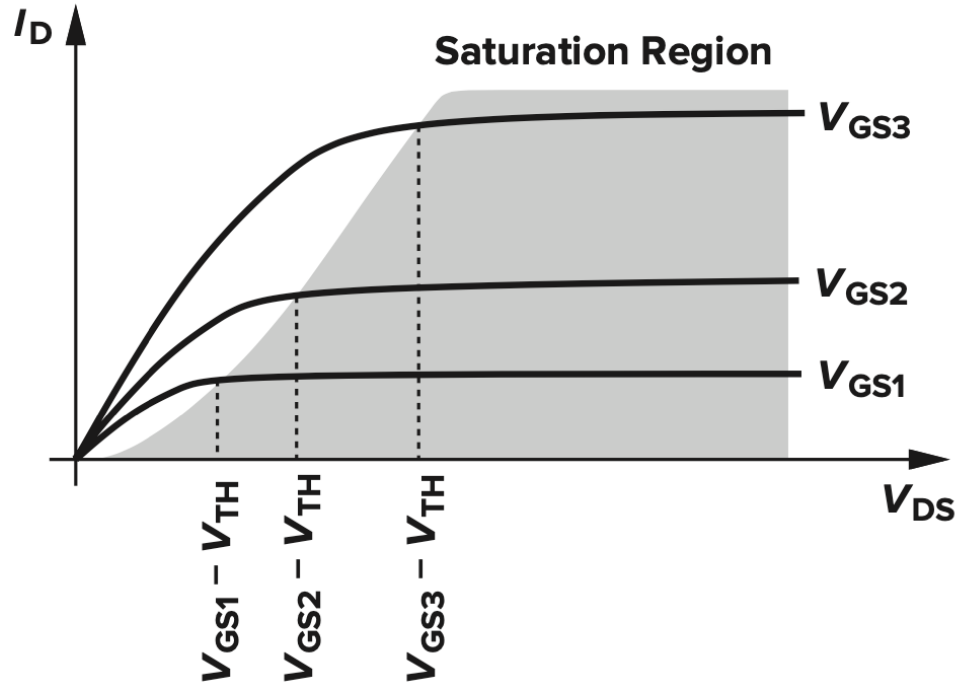


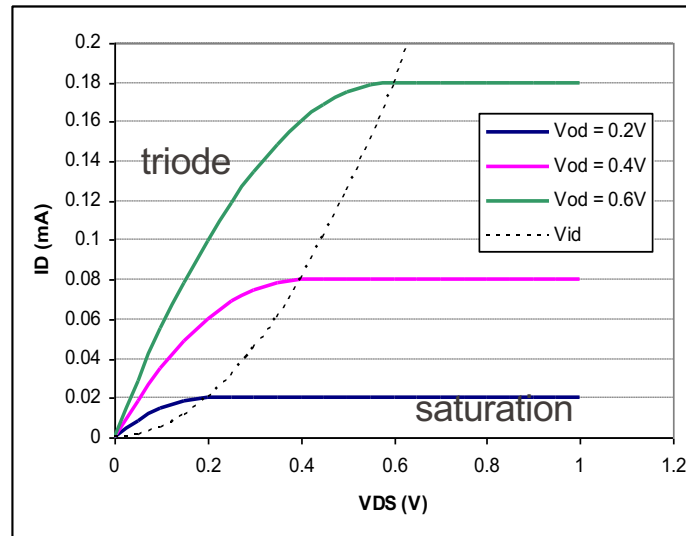
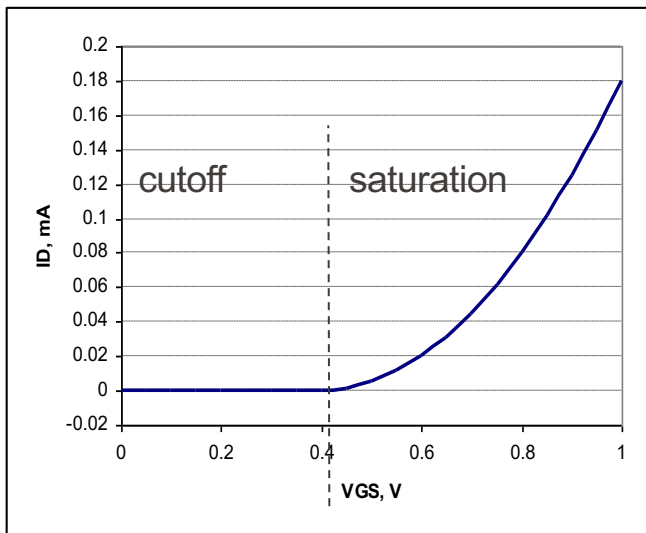
$$V_{DS} > V_{GS} - V_{TH}$$

- I_D is relatively **constant with V_{DS}** , and the device operates in the “**saturation**” region.



$$I_D \approx \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2$$

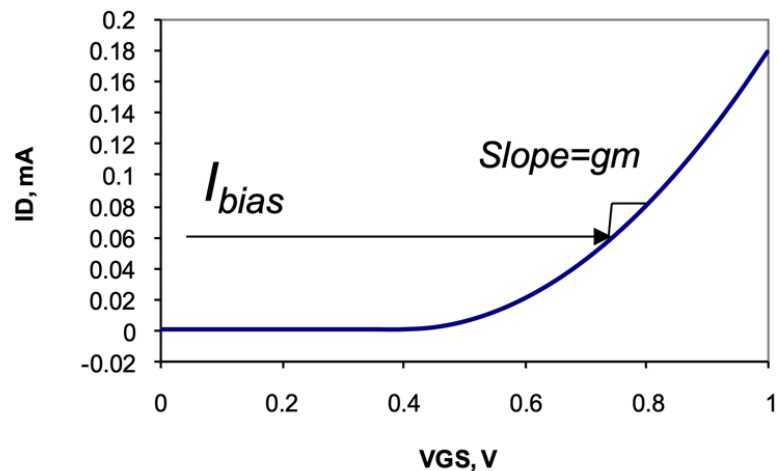


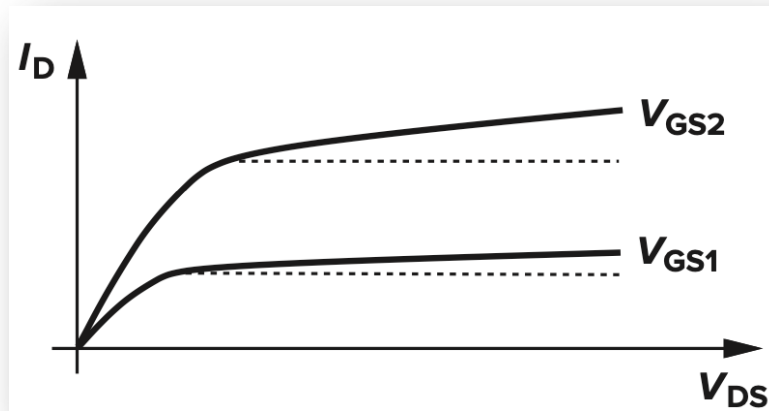


MOS transconductance (g_m) in saturation

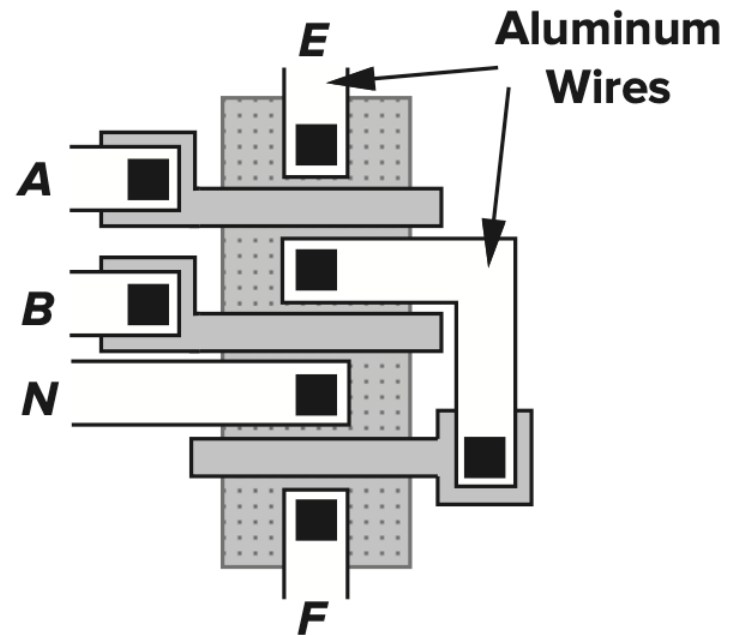
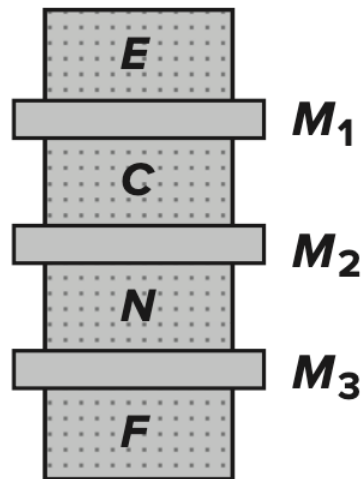
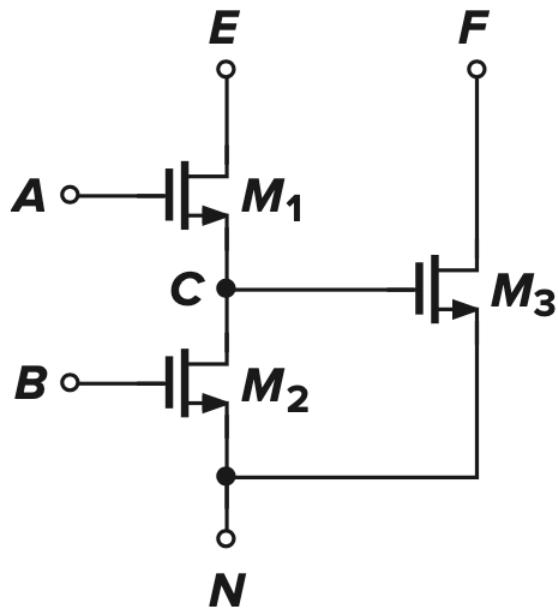
$$g_m = \left. \frac{\partial I_D}{\partial V_{GS}} \right|_{V_{DS} \text{ const.}}$$
$$= \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})$$

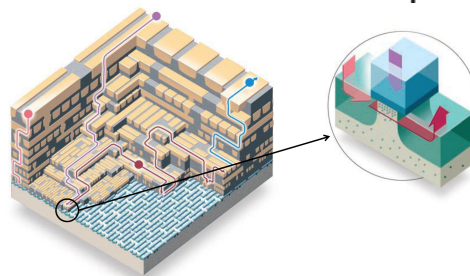
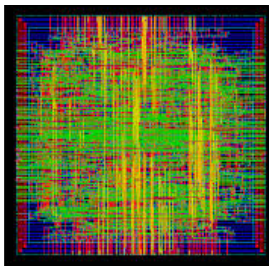
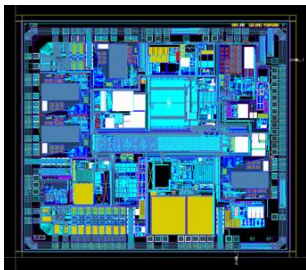
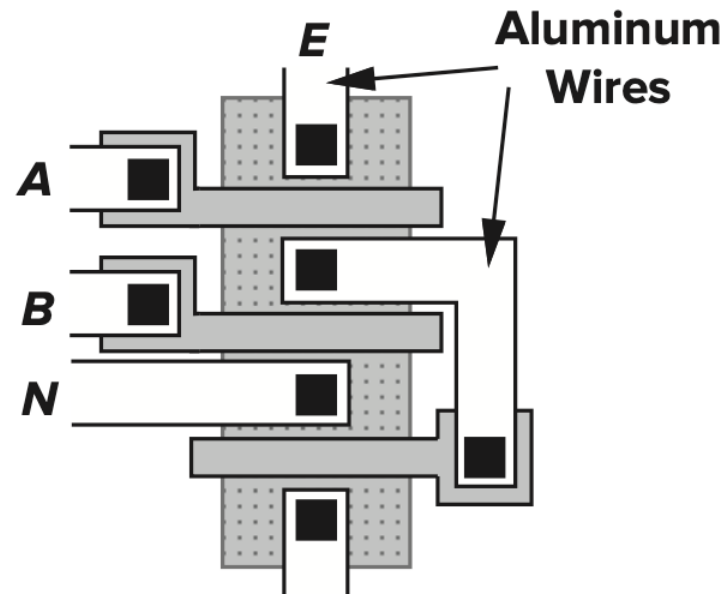
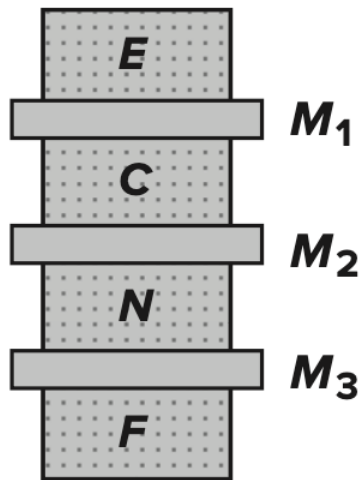
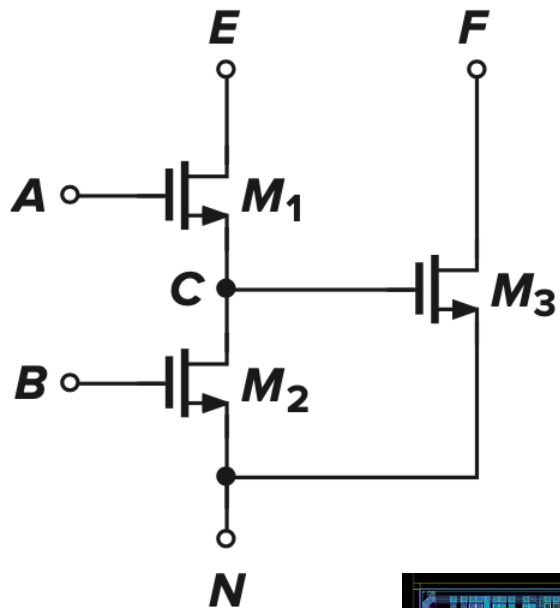
$$I_D \approx \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2$$

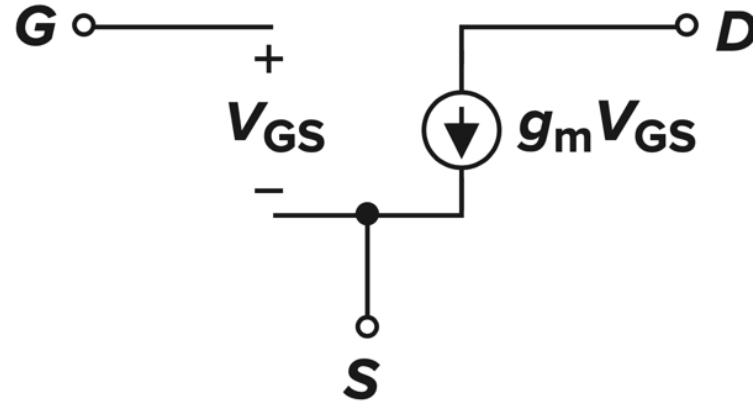


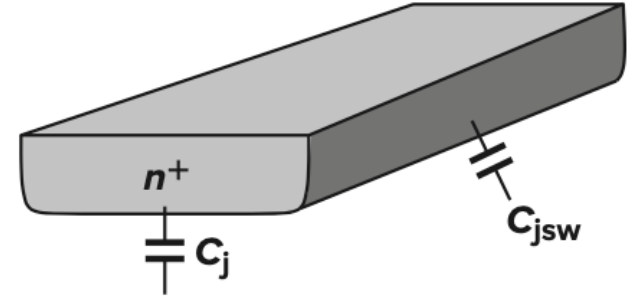
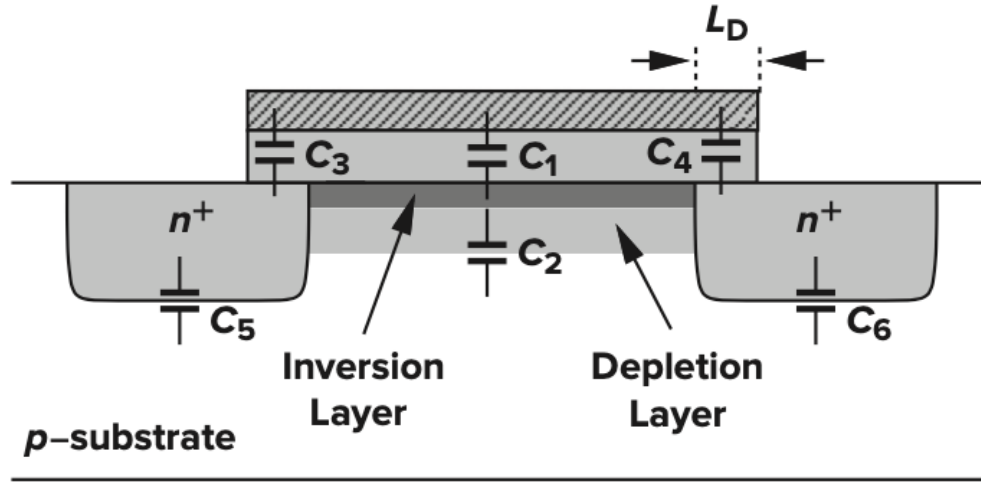


$$I_D \approx \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2 (1 + \lambda V_{DS})$$



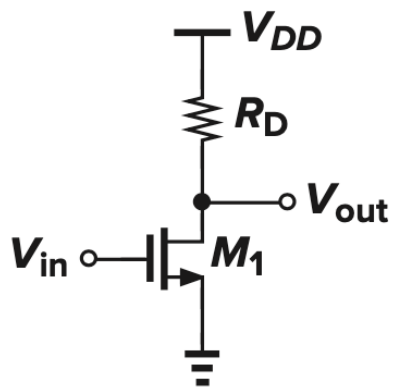




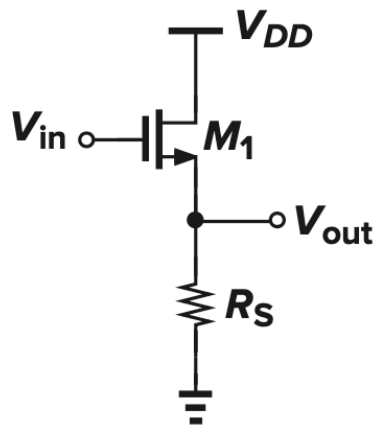


- (1) the **oxide** capacitance between the **gate** and the **channel** C_1
- (2) the **depletion** capacitance between the channel and the substrate C_2
- (3) the capacitance due to **overlap** of the **gate** poly with **source** and **drain**, C_3 and C_4
- (4) The **junction capacitance** between the **S/D** areas and the **substrate**, two components: the **bottom-plate capacitance** at the bottom of the junction C_j , and the **sidewall capacitance** due to the perimeter of the junction, C_{jsw}

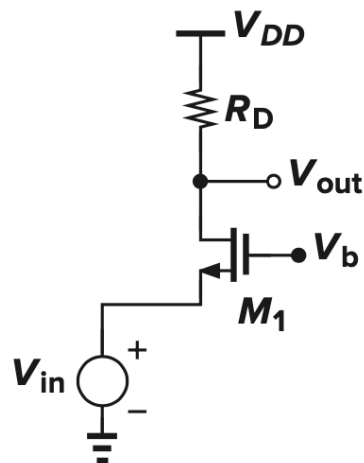
Common-Source Stage



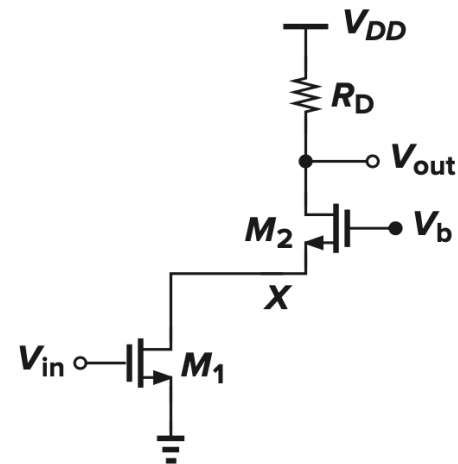
Source Follower

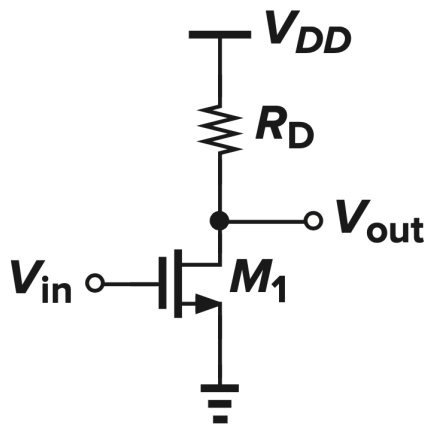


Common-Gate Stage

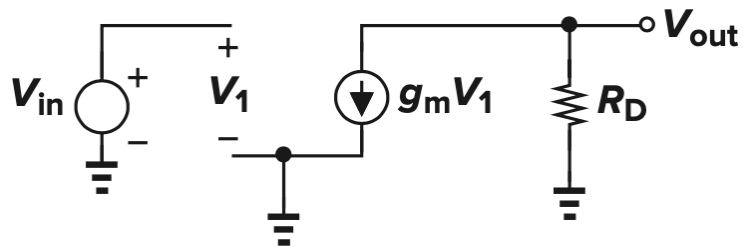


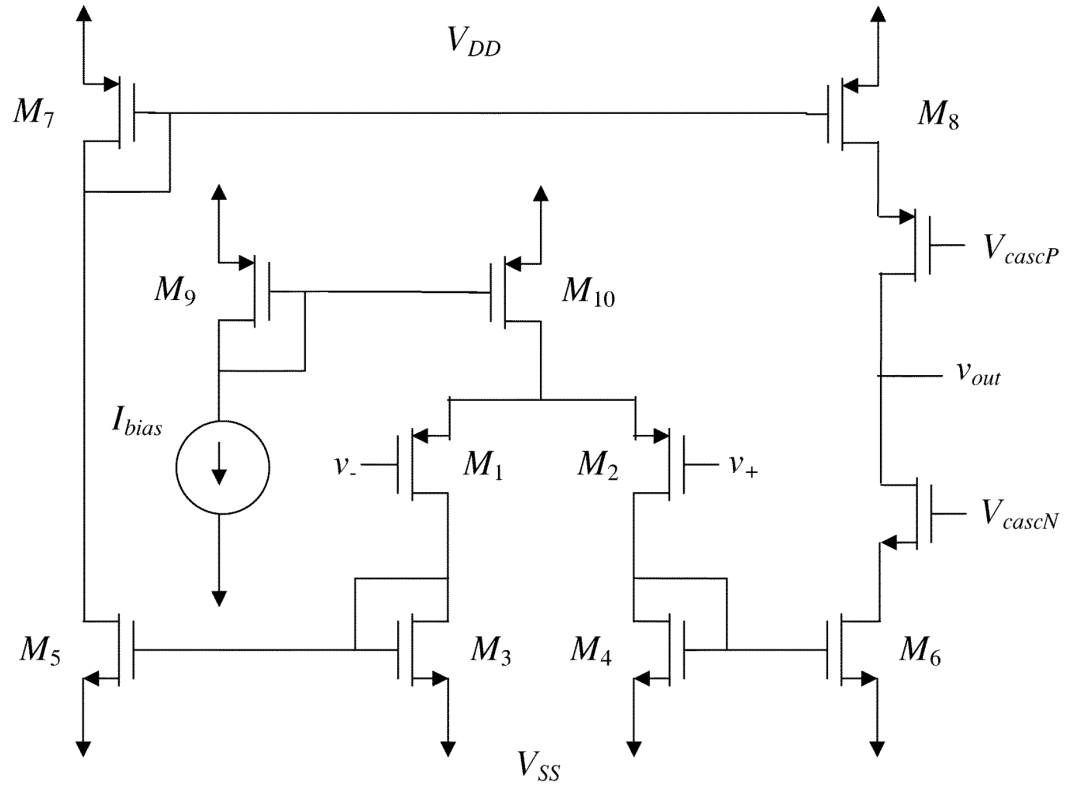
Cascode



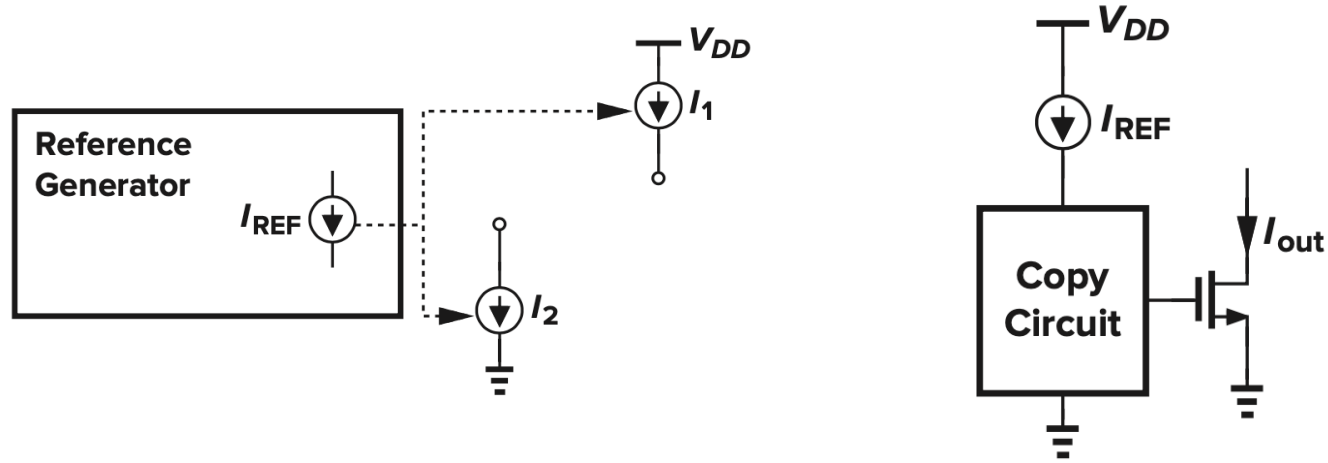


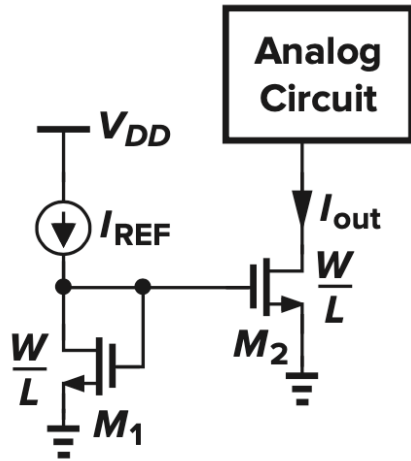
small-signal model:





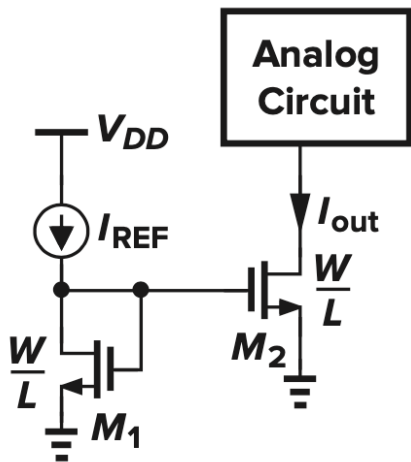
Copying current from a reference





(neglecting channel-length modulation)

Basic current mirror circuit



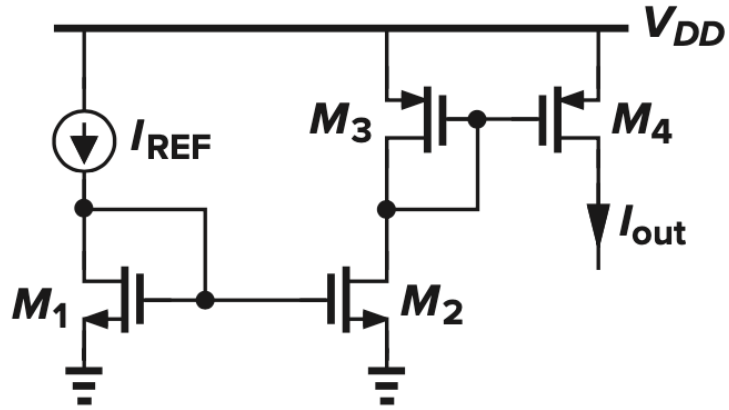
(neglecting channel-length modulation)

$$I_{REF} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L} \right)_1 (V_{GS} - V_{TH})^2$$

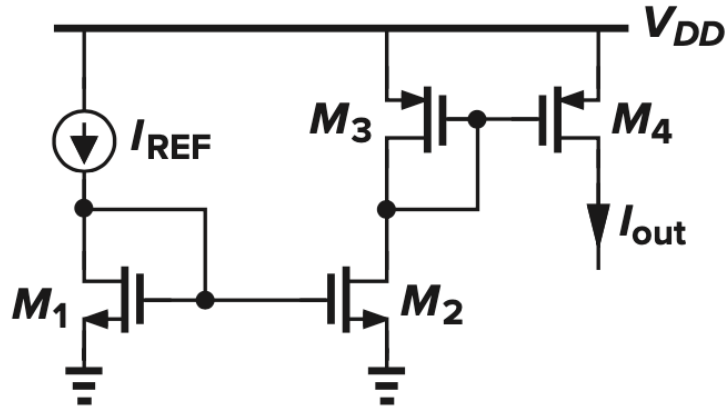
$$I_{out} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L} \right)_2 (V_{GS} - V_{TH})^2$$



$$I_{out} = \frac{(W/L)_2}{(W/L)_1} I_{REF}$$



Basic current mirror circuit: example



$$I_{D2} = I_{REF}[(W/L)_2/(W/L)_1]$$

$$I_{D4} = I_{D3} \times [(W/L)_4/(W/L)_3]$$

$$\alpha = \beta = 5 \quad \rightarrow \quad I_{REF} \times 25$$